

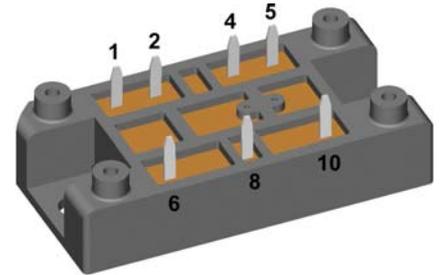
Standard Rectifier Module

3~ Rectifier	
V_{RRM} =	800 V
I_{DAV} =	45 A
I_{FSM} =	300 A

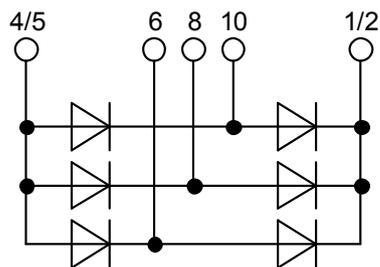
3~ Rectifier Bridge

Part number

VUO34-08NO1



 E72873



Features / Advantages:

- Package with DCB ceramic
- Reduced weight
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

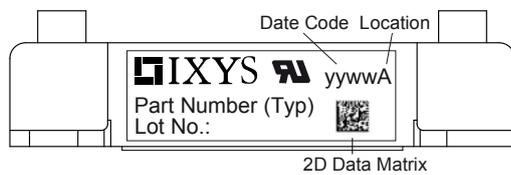
- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: V1-A-Pack

- Isolation Voltage: 3600V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			900	V	
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			800	V	
I_R	reverse current	$V_R = 800 V$	$T_{VJ} = 25^{\circ}C$		20	μA	
		$V_R = 800 V$	$T_{VJ} = 150^{\circ}C$		1	mA	
V_F	forward voltage drop	$I_F = 15 A$	$T_{VJ} = 25^{\circ}C$		1.13	V	
					1.46	V	
		$I_F = 45 A$	$T_{VJ} = 125^{\circ}C$		1.06	V	
					1.48	V	
I_{DAV}	bridge output current	$T_C = 110^{\circ}C$ rectangular $d = 1/3$	$T_{VJ} = 150^{\circ}C$		45	A	
V_{FO}	threshold voltage		$T_{VJ} = 150^{\circ}C$		0.81	V	
r_F	slope resistance				14.9	m Ω	
R_{thJC}	thermal resistance junction to case				1.7	K/W	
R_{thCH}	thermal resistance case to heatsink			0.4		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		70	W	
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		300	A	
					325	A	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$	$T_{VJ} = 150^{\circ}C$		255	A
						275	A
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		450	A ² s	
					440	A ² s	
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$	$T_{VJ} = 150^{\circ}C$		325	A ² s
						315	A ² s
C_J	junction capacitance	$V_R = 400 V; f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		11	pF	

Package V1-A-Pack			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{stg}	storage temperature		-40		125	°C
T_{VJ}	virtual junction temperature		-40		150	°C
Weight				37		g
M_D	mounting torque		2		2.5	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V

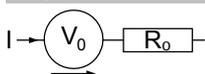


Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO34-08NO1	VUO34-08NO1	Box	10	461113

Equivalent Circuits for Simulation

* on die level

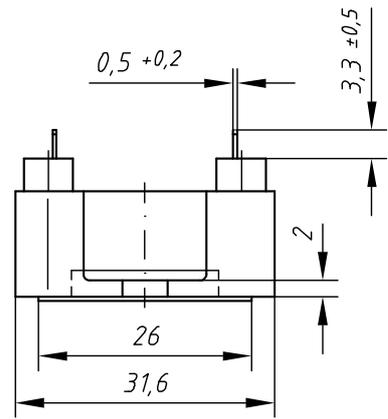
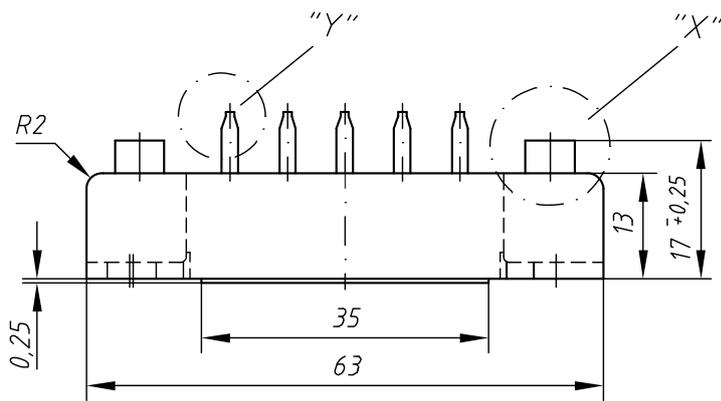
$T_{VJ} = 150\text{ °C}$



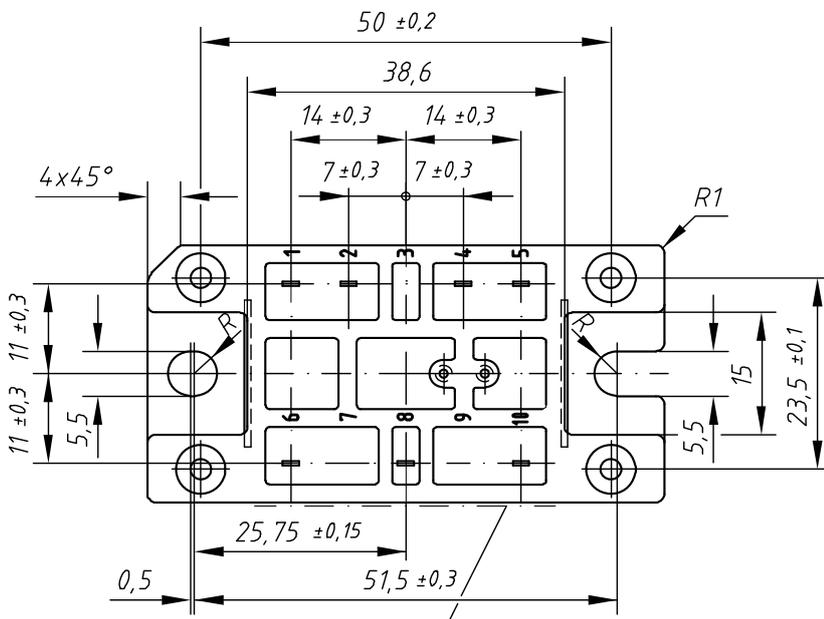
Rectifier

$V_{0\ max}$	threshold voltage	0.81	V
$R_{0\ max}$	slope resistance *	13.7	mΩ

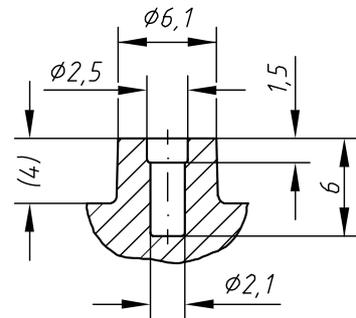
Outlines V1-A-Pack



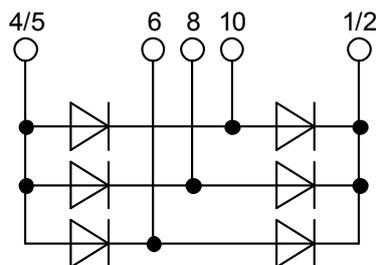
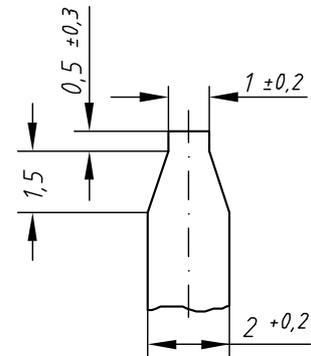
Detail "X" M 2:1



Aufdruck der Typenbezeichnung



Detail "Y" M 5:1



Rectifier

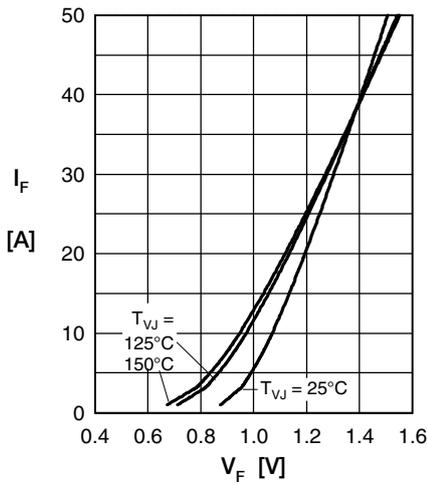


Fig. 1 Forward current vs. voltage drop per diode

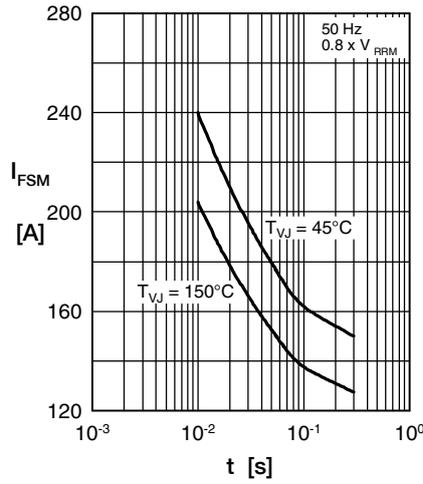


Fig. 2 Surge overload current vs. time per diode

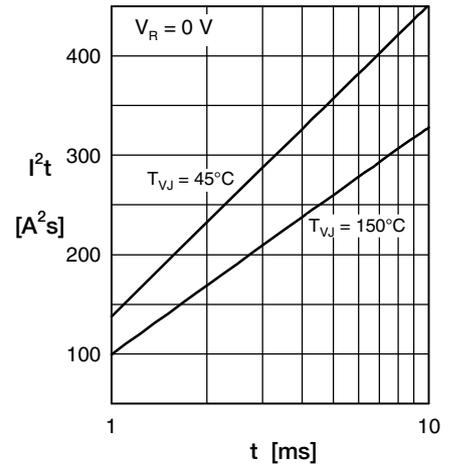


Fig. 3 I²t vs. time per diode

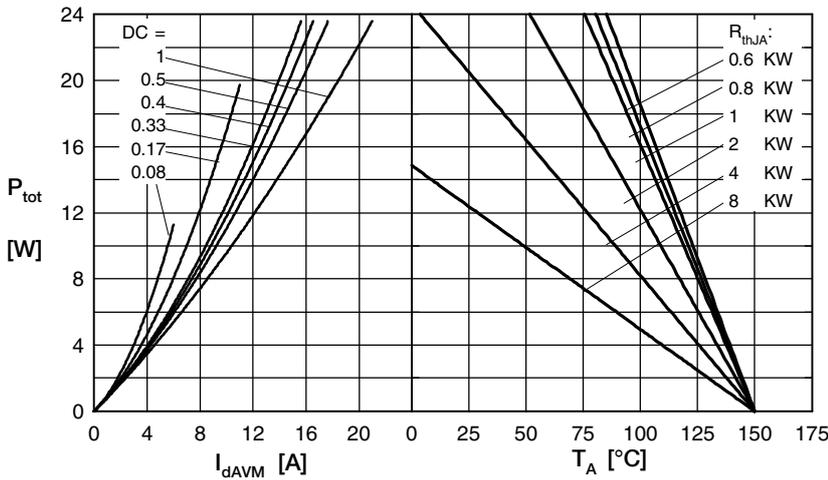


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

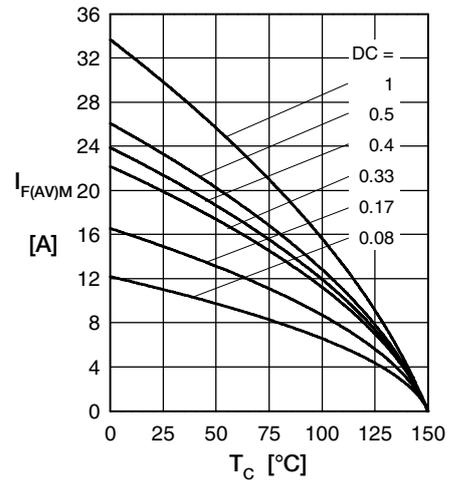


Fig. 5 Max. forward current vs. case temperature per diode

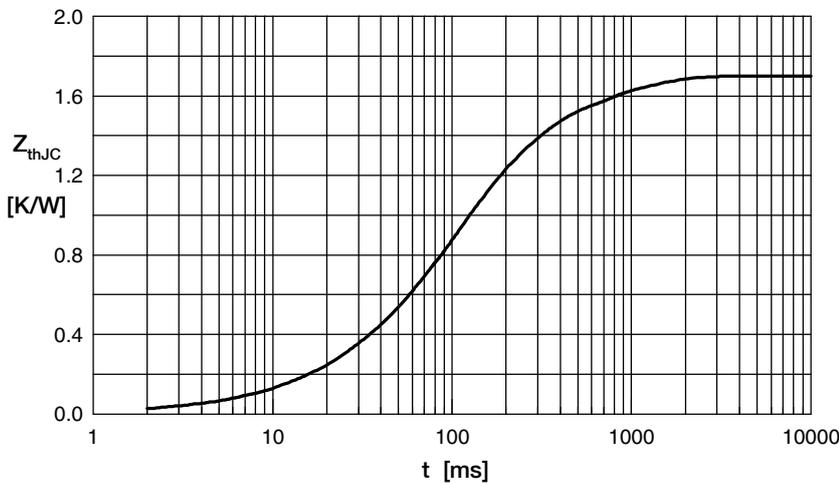


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R _{th} (K/W)	t _i (s)
1	1.150	0.1015
2	0.150	0.1026
3	0.100	0.4919
4	0.300	0.6200